EMIPAK 2B PressFit Power Module
3-Levels Half Bridge Inverter Stage, 150 A

EMIPAK 2B
(package example)

PRIMARY CHARACTERISTICS

Q1 - Q4 IGBT STAGE	
V_{CES}	650 V
$V_{CE(on)}$ typical at I_C = 100 A	1.72 V
Q2 - Q3 IGBT STAGE	
V_{CES}	650 V
$V_{CE(on)}$ typical at I_C = 150 A	1.75 V
I_C at T_C = 82 °C	150 A
Speed	8 kHz to 30 kHz
Package	EMIPAK 2B
Circuit configuration	3-levels half bridge inverter stage

FEATURES

- Trench IGBT technology
- FRED Pt® clamping diodes
- PressFit pins technology
- Exposed Al_2O_3 substrate with low thermal resistance
- Short circuit rated
- Square RBSOA
- Integrated thermistor
- Low internal inductances
- Low switching loss
- UL approved file E78996
- PressFit pins locking technology PATENT(S): www.vishay.com/patents
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS
COMPLIANT

DESCRIPTION

VS-ETF150Y65U is an integrated solution for a multi level inverter stage in a single package. The EMIPAK 2B package is easy to use thanks to the PressFit pins and the exposed substrate provides improved thermal performance. The optimized layout also helps to minimize stray parameters, allowing for better EMI performance.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Operating junction temperature	T_J		175	°C
Storage temperature range	T_{Stg}		-40 to +150	
RMS isolation voltage	V_{ISOL}	T_J = 25 °C, all terminals shorted, f = 50 Hz, t = 1 s	3500	V
Q1 - Q4 IGBT				
Collector to emitter voltage	V_{CES}		650	V
Gate to emitter voltage	V_{GES}		20	
Pulsed collector current	I_{CM}		220	A
Clamped inductive load current	I_{LM} (1)		220	
Continuous collector current	I_C	T_C = 25 °C	142	A
		T_C = 60 °C	121	
		T_{SINK} = 60 °C	64	
Power dissipation	P_D	T_C = 25 °C	417	W
		T_C = 60 °C	319	

PATENT(S): www.vishay.com/patents
This Vishay product is protected by one or more United States and International patents.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MAX.**	**UNITS**
Q2 - Q3 IGBT				
Collector to emitter voltage	V_{CES}		650	V
Gate to emitter voltage	V_{GES}		20	
Pulsed collector current	I_{CM}		300	A
Clamped inductive load current	I_{LM} [(1)]		300	
Continuous collector current	I_C	T_C = 25 °C	201	A
		T_C = 60 °C	171	
		T_{SINK} = 60 °C	77	
Power dissipation	P_D	T_C = 25 °C	600	W
		T_C = 60 °C	460	
D5 - D6 CLAMPING DIODE				
Repetitive peak reverse voltage	V_{RRM}		650	V
Single pulse forward current	I_{FSM}	10 ms sine or 6 ms rectangular pulse, T_J = 25 °C	380	A
Diode continuous forward current	I_F	T_C = 25 °C	95	
		T_C = 60 °C	80	
		T_{SINK} = 60 °C	45	
Power dissipation	P_D	T_C = 25 °C	221	W
		T_C = 60 °C	169	
D1 - D2 - D3 - D4 AP DIODE				
Single pulse forward current	I_{FSM}	10 ms sine or 6 ms rectangular pulse, T_J = 25 °C	250	A
Diode continuous forward current	I_F	T_C = 25 °C	78	
		T_C = 60 °C	66	
		T_{SINK} = 60 °C	43	
Power dissipation	P_D	T_C = 25 °C	176	W
		T_C = 60 °C	135	

Notes

- Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur

(1) V_{CC} = 325 V, V_{GE} = 15 V, L = 500 µH, R_g = 4.7 Ω, T_J = 175 °C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Q1 - Q4 IGBT						
Collector to emitter breakdown voltage	BV_{CES}	V_{GE} = 0 V, I_C = 100 µA	650	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	V_{GE} = 15 V, I_C = 100 A	-	1.72	2.06	
		V_{GE} = 15 V, I_C = 100 A, T_J = 125 °C	-	1.94	-	
Gate threshold voltage	$V_{GE(th)}$	V_{CE} = V_{GE}, I_C = 3.3 mA	5.0	6.3	8.4	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	V_{CE} = V_{GE}, I_C = 1 mA (25 °C to 125 °C)	-	-19	-	mV/°C
Forward transconductance	g_{fe}	V_{CE} = 20 V, I_C = 100 A	-	71	-	S
Transfer characteristics	V_{GE}	V_{CE} = 20 V, I_C = 100 A	-	10.5	-	V
Zero gate voltage collector current	I_{CES}	V_{GE} = 0 V, V_{CE} = 650 V	-	0.2	100	µA
		V_{GE} = 0 V, V_{CE} = 650 V, T_J = 125 °C	-	60	-	
Gate to emitter leakage current	I_{GES}	V_{GE} = ± 20 V, V_{CE} = 0 V	-	-	± 600	nA

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Q2 - Q3 IGBT						
Collector to emitter breakdown voltage	BV_{CES}	V_{GE} = 0 V, I_C = 100 µA	650	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	V_{GE} = 15 V, I_C = 150 A	-	1.75	2.17	
		V_{GE} = 15 V, I_C = 150 A, T_J = 125 °C	-	1.99	-	
Gate threshold voltage	$V_{GE(th)}$	V_{CE} = V_{GE}, I_C = 5.0 mA	5.0	5.9	8.4	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	V_{CE} = V_{GE}, I_C = 1.0 mA (25 °C to 125 °C)	-	-19	-	mV/°C
Forward transconductance	g_{fe}	V_{CE} = 20 V, I_C = 150 A	-	102	-	S
Transfer characteristics	V_{GE}	V_{CE} = 20 V, I_C = 150 A	-	9.8	-	V
Zero gate voltage collector current	I_{CES}	V_{GE} = 0 V, V_{CE} = 650 V	-	0.2	100	µA
		V_{GE} = 0 V, V_{CE} = 650 V, T_J = 125 °C	-	100	-	
Gate to emitter leakage current	I_{GES}	V_{GE} = ± 20 V, V_{CE} = 0 V	-	-	± 600	nA
D5 - D6 CLAMPING DIODE						
Cathode to anode blocking voltage	V_{BR}	I_R = 100 µA	650	-	-	V
Forward voltage drop	V_{FM}	I_F = 100 A	-	2.3	3.15	
		I_F = 100 A, T_J = 125 °C	-	1.6	-	
Reverse leakage current	I_{RM}	V_R = 650 V	-	0.2	75	µA
		V_R = 650 V, T_J = 125 °C	-	110	-	
D1 - D2 - D3 - D4 AP DIODE						
Forward voltage drop	V_{FM}	I_F = 100 A	-	2.14	3.18	V
		I_F = 100 A, T_J = 125 °C	-	1.79	-	

SWITCHING CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Q1 - Q4 IGBT (WITH D5 - D6 CLAMPING DIODE)						
Total gate charge (turn-on)	Q_g	I_C = 100 A V_{CC} = 400 V V_{GE} = 15 V	-	190	-	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	65	-	
Gate to collector charge (turn-on)	Q_{gc}		-	80	-	
Turn-on switching loss	E_{on}	I_C = 100 A V_{CC} = 325 V V_{GE} = 15 V R_g = 4.7 Ω L = 500 µH (1)	-	0.43	-	mJ
Turn-off switching loss	E_{off}		-	1.04	-	
Total switching loss	E_{tot}		-	1.47	-	
Turn-on delay time	$t_{d(on)}$		-	113	-	ns
Rise time	t_r		-	50	-	
Turn-off delay time	$t_{d(off)}$		-	108	-	
Fall time	t_f		-	57	-	
Turn-on switching loss	E_{on}	I_C = 100 A V_{CC} = 325 V V_{GE} = 15 V R_g = 4.7 Ω L = 500 µH T_J = 125 °C (1)	-	0.61	-	mJ
Turn-off switching loss	E_{off}		-	1.49	-	
Total switching loss	E_{tot}		-	2.1	-	
Turn-on delay time	$t_{d(on)}$		-	113	-	ns
Rise time	t_r		-	51	-	
Turn-off delay time	$t_{d(off)}$		-	117	-	
Fall time	t_f		-	79	-	
Input capacitance	C_{ies}	V_{GE} = 0 V V_{CC} = 30 V f = 1 MHz	-	6600		pF
Output capacitance	C_{oes}		-	340		
Reverse transfer capacitance	C_{res}		-	180		
Reverse bias safe operating area	RBSOA	T_J = 175 °C, I_C = 220 A V_{CC} = 325 V, V_P = 650 V R_g = 4.7 Ω, V_{GE} = 15 V to 0 V	Fullsquare			
Short circuit safe operating area	SCSOA	R_g = 5.0 Ω, V_{CC} = 400 V, V_P = 600 V V_{GE} = 15 V to 0, T_J = 150 °C	-	-	5.5	µs

SWITCHING CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Q2 - Q3 IGBT (WITH D2 - D3 AP DIODE)						
Total gate charge (turn-on)	Q_g	I_C = 150 A V_{CC} = 400 V V_{GE} = 15 V	-	310	-	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	95	-	
Gate to collector charge (turn-on)	Q_{gc}		-	130	-	
Turn-on switching loss	E_{on}	I_C = 150 A V_{CC} = 325 V V_{GE} = 15 V R_g = 4.7 Ω L = 500 µH (1)	-	0.49	-	mJ
Turn-off switching loss	E_{off}		-	2.51	-	
Total switching loss	E_{tot}		-	3.0	-	
Turn-on delay time	$t_{d(on)}$		-	162	-	ns
Rise time	t_r		-	71	-	
Turn-off delay time	$t_{d(off)}$		-	148	-	
Fall time	t_f		-	64	-	
Turn-on switching loss	E_{on}	I_C = 150 A V_{CC} = 325 V V_{GE} = 15 V R_g = 4.7 Ω L = 500 µH T_J = 125 °C (1)	-	0.62	-	mJ
Turn-off switching loss	E_{off}		-	3.18	-	
Total switching loss	E_{tot}		-	3.8	-	
Turn-on delay time	$t_{d(on)}$		-	162	-	ns
Rise time	t_r		-	75	-	
Turn-off delay time	$t_{d(off)}$		-	153	-	
Fall time	t_f		-	81	-	
Input capacitance	C_{ies}	V_{GE} = 0 V V_{CC} = 30 V f = 1 MHz	-	9900	-	pF
Output capacitance	C_{oes}		-	460	-	
Reverse transfer capacitance	C_{res}		-	250	-	
Reverse bias safe operating area	RBSOA	T_J = 175 °C, I_C = 300 A V_{CC} = 325 V, V_P = 650 V R_g = 4.7 Ω, V_{GE} = 15 V to 0 V	Fullsquare			
Short circuit safe operating area	SCSOA	R_g = 5.0 Ω, V_{CC} = 400 V, V_P = 600 V V_{GE} = 15 V to 0, T_J = 150 °C	-	-	5.5	µs
D5 - D6 CLAMPING DIODE						
Diode reverse recovery time	t_{rr}	V_R = 200 V I_F = 50 A dI/dt = 500 A/µs	-	55	-	ns
Diode peak reverse current	I_{rr}		-	8.7	-	A
Diode recovery charge	Q_{rr}		-	242	-	nC
Diode reverse recovery time	t_{rr}	V_R = 200 V I_F = 50 A dI/dt = 500 A/µs, T_J = 125 °C	-	112	-	ns
Diode peak reverse current	I_{rr}		-	21	-	A
Diode recovery charge	Q_{rr}		-	1177	-	nC
D1 - D2 - D3 - D4 AP DIODE						
Diode reverse recovery time	t_{rr}	V_R = 200 V I_F = 50 A dI/dt = 500 A/µs	-	66	-	ns
Diode peak reverse current	I_{rr}		-	11	-	A
Diode recovery charge	Q_{rr}		-	363	-	nC
Diode reverse recovery time	t_{rr}	V_R = 200 V I_F = 50 A dI/dt = 500 A/µs, T_J = 125 °C	-	130	-	ns
Diode peak reverse current	I_{rr}		-	21.3	-	A
Diode recovery charge	Q_{rr}		-	1392	-	nC

Note

(1) Energy losses include “tail” and diode reverse recovery

INTERNAL NTC - THERMISTOR SPECIFICATIONS				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUE**	**UNITS**
Resistance	R25	T_C = 25 °C	5000	Ω
	R100	T_C = 100 °C	493 ± 5 %	
B-value	$B_{25/50}$	$R_2 = R_{25}$ exp. $[B_{25/50}$ $(1/T_2$ - 1/(298.15 K))]	3375 ± 5 %	K
Maximum operating temperature			220	°C
Dissipation constant			2	mW/°C
Thermal time constant			8	s

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Q1 - Q4 IGBT - junction to case thermal resistance (per switch)	R_{thJC}	-	-	0.36	°C/W
Q2 - Q3 IGBT - junction to case thermal resistance (per switch)		-	-	0.25	
D5 - D6 clamping diode - junction to case thermal resistance (per diode)		-	-	0.68	
D1 - D2 - D3 - D4 AP diode - junction to case thermal resistance (per diode)		-	-	0.85	
Q1 - Q4 IGBT - case to sink thermal resistance (per switch)	R_{thCS} (1)	-	0.63	-	
Q2 - Q3 IGBT - case to sink thermal resistance (per switch)		-	0.62	-	
D5 - D6 clamping diode - case to sink thermal resistance (per diode)		-	1.0	-	
D1 - D2 - D3 - D4 AP diode - case to sink thermal resistance (per diode)		-	0.78	-	
Case to sink thermal resistance per module		-	0.08	-	°C/W
Mounting torque (M4)		2	-	3	Nm
Weight		-	45	-	g

Note

(1) Mounting surface flat, smooth, and greased

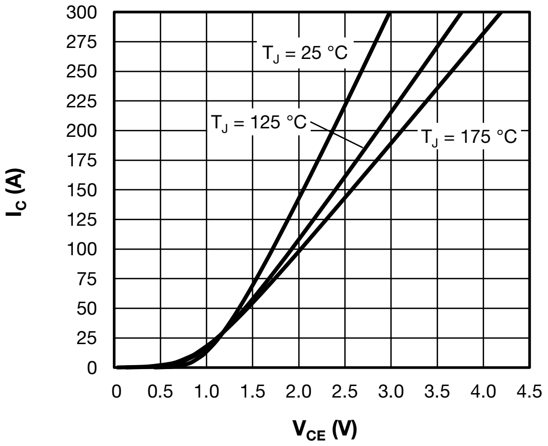


Fig. 1 - I_C vs. V_{CE},
Typical Q1 - Q4 Trench IGBT Output Characteristics, V_{GE} = 15 V

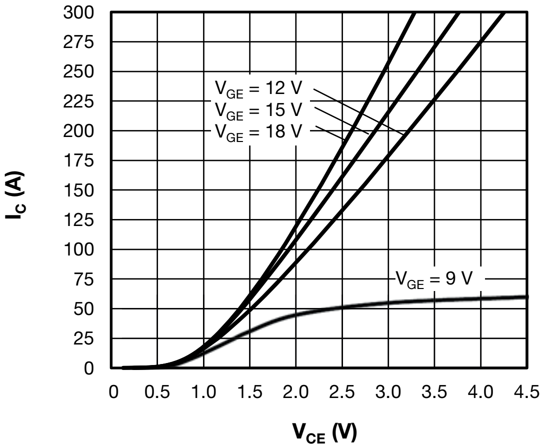


Fig. 2 - I_C vs. V_{CE}
Typical Q1 - Q4 Trench IGBT Output Characteristics, T_J = 125 °C

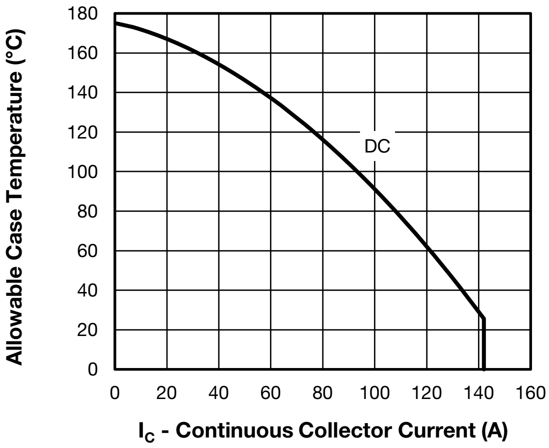


Fig. 3 - Allowable Case Temperature vs. Continuous Collector Current, Maximum Q1 - Q4 IGBT Continuous Collector Current vs. Case Temperature

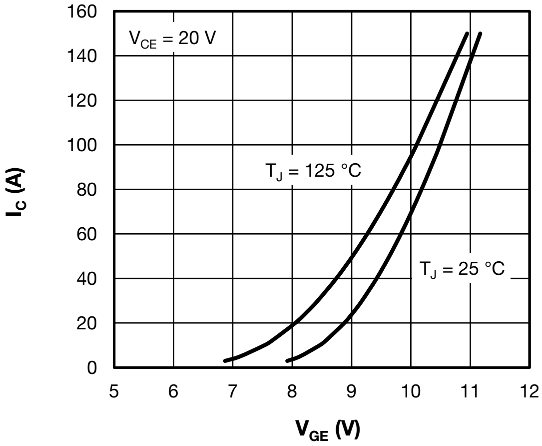


Fig. 4 - I_C vs V_{GE}
Typical Q1 - Q4 Trench IGBT Transfer Characteristics

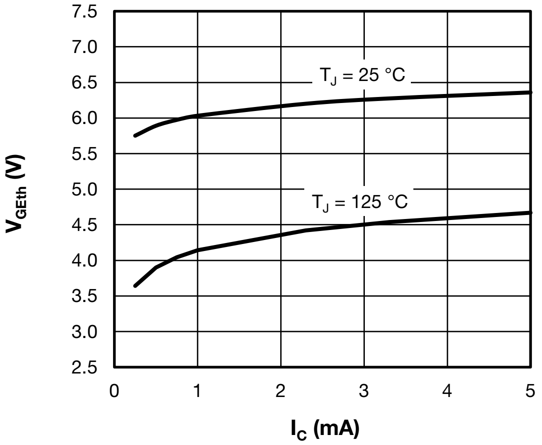


Fig. 5 - V_{GEth} vs. I_C
Typical Q1 - Q4 Trench IGBT Gate Threshold Voltage

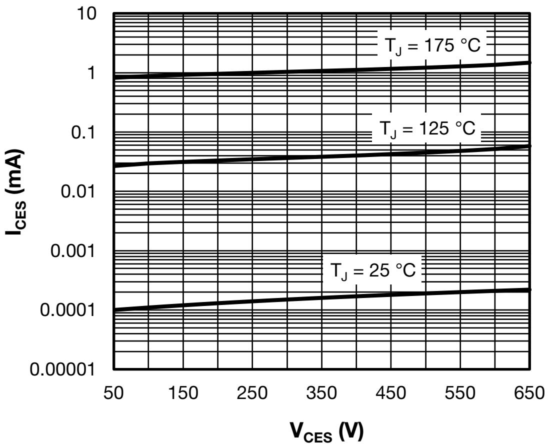


Fig. 6 - I_{CES} vs V_{CES}
Typical Q1 - Q4 Trench IGBT Zero Gate Voltage Collector Current

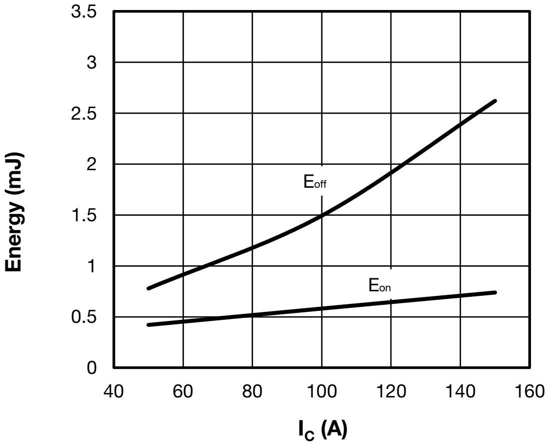


Fig. 7 - Energy Loss vs. I_C
(Typical Q1 - Q4 Trench IGBT Energy Loss vs. I_C (with D5 - D6 Clamping Diode)), $T_J = 125\,°C$, $V_{CC} = 325\,V$, $R_g = 4.7\,\Omega$, $V_{GE} = \pm\ 15\ V$, L = 500 μH

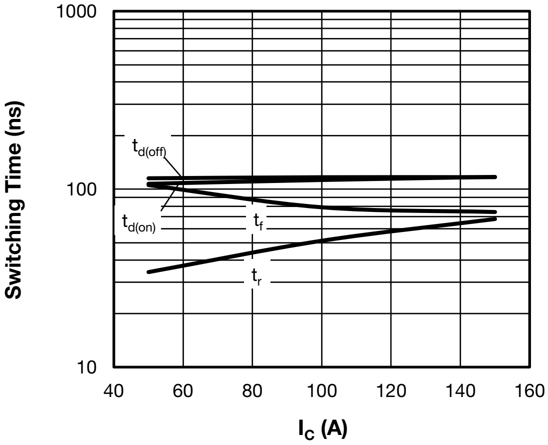


Fig. 8 - Switching Time vs. I_C
(Typical Q1 - Q4 Trench IGBT Switching Time vs. I_C (with D5 - D6 Clamping Diode)), $T_J = 125\,°C$, $V_{CC} = 325\,V$, $R_g = 4.7\,\Omega$, $V_{GE} = \pm\ 15\ V$, L = 500 μH

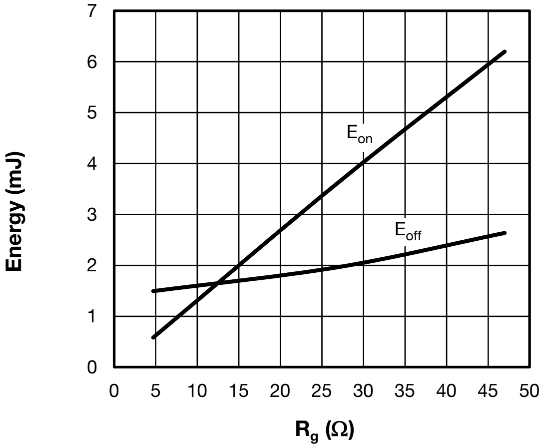


Fig. 9 - Energy Loss vs. R_g
(Typical Q1 - Q4 Trench IGBT Energy Loss vs R_g (with D5 - D6 Clamping Diode)), $T_J = 125\,°C$, $V_{CC} = 325\,V$, $I_C = 100\,A$, $V_{GE} = \pm 15\,V$, L = 500 μH

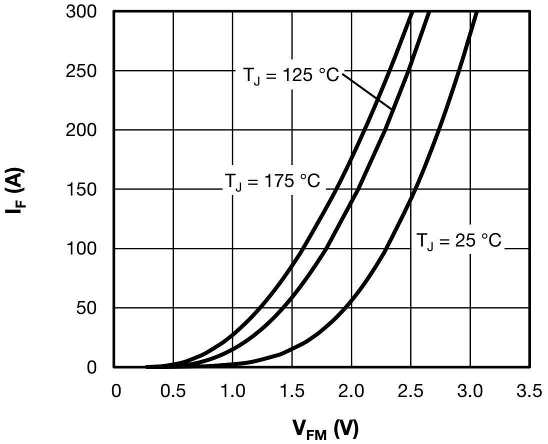


Fig. 12 - I_F vs. V_{FM}
(Typical D5 - D6 Clamping Diode Forward Characteristics)

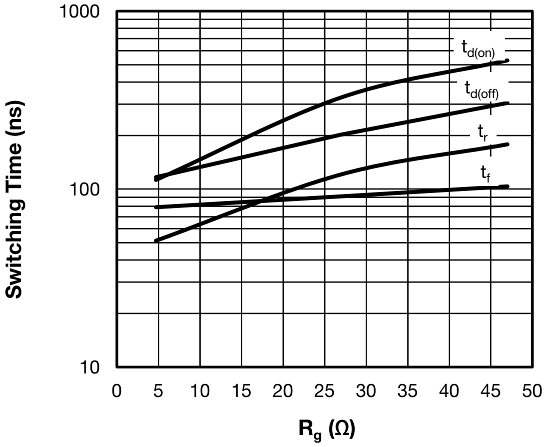


Fig. 10 - Switching Time vs. R_g
(Typical Q1 - Q4 Trench IGBT Switching Time vs. R_g (with D5 - D6 Clamping Diode)), $T_J = 125\,°C$, $V_{CC} = 325\,V$, $I_C = 100\,A$, $V_{GE} = \pm 15\,V$, L = 500 μH

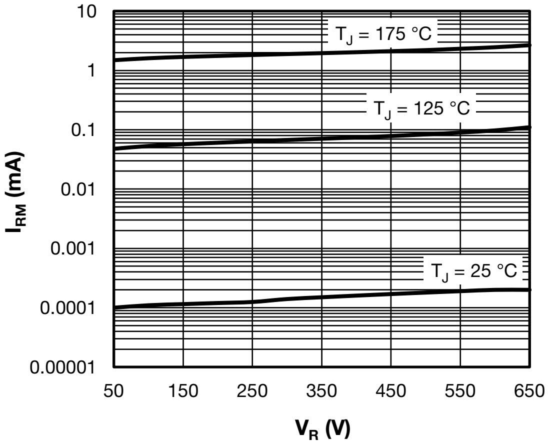


Fig. 13 - I_{RM} vs. V_R
(Typical D5 - D6 Clamping Diode Reverse Leakage Current)

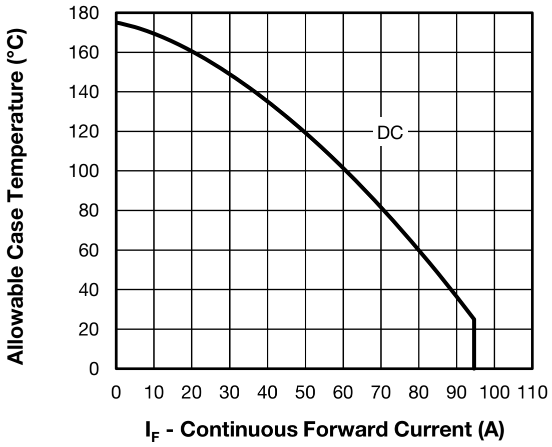


Fig. 11 - Allowable Case Temperature vs. Continuous Collector Current, (Maximum D5 - D6 Diode Continuous Forward Current vs. Case Temperature)

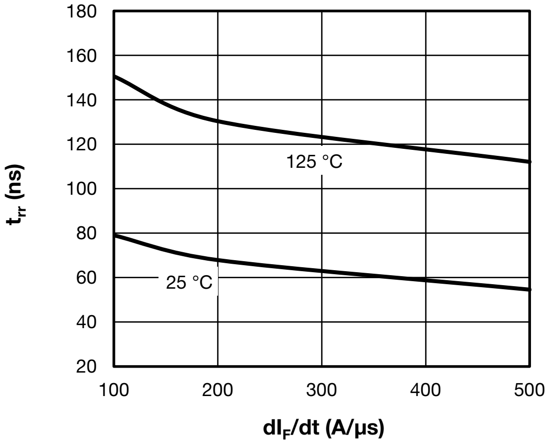


Fig. 14 - t_{rr} vs. dI_F/dt
(Typical D5 - D6 Clamping Diode Reverse Recovery Time vs. dI_F/dt), $V_{rr} = 200\,V$, $I_F = 50\,A$

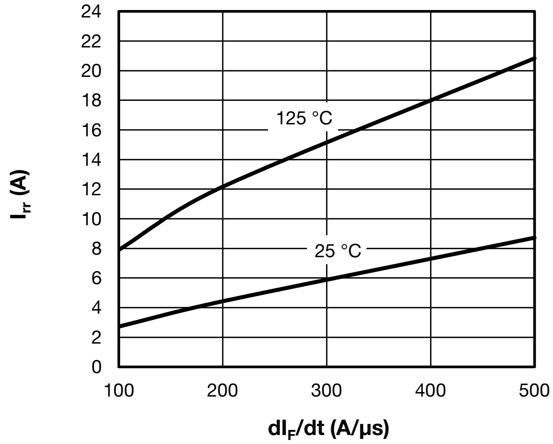


Fig. 15 - I_{rr} vs. dI_F/dt)
(Typical D5 - D6 Clamping Diode Reverse Recovery Current vs. dI_F/dt), V_{rr} = 200 V, I_F = 50 A

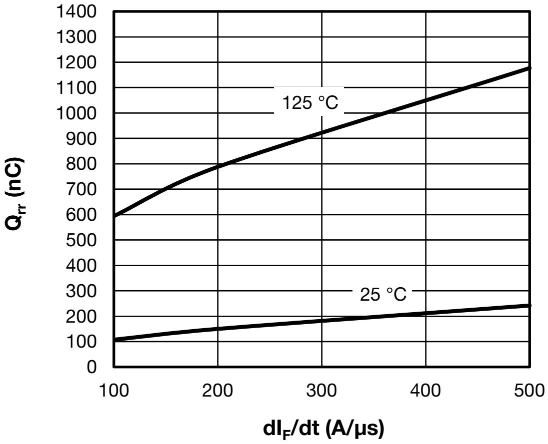


Fig. 16 - Q_{rr} vs. dI_F/dt)
(Typical D5 - D6 Clamping Diode Reverse Recovery Charge vs. dI_F/dt)), V_{rr} = 200 V, I_F = 50 A

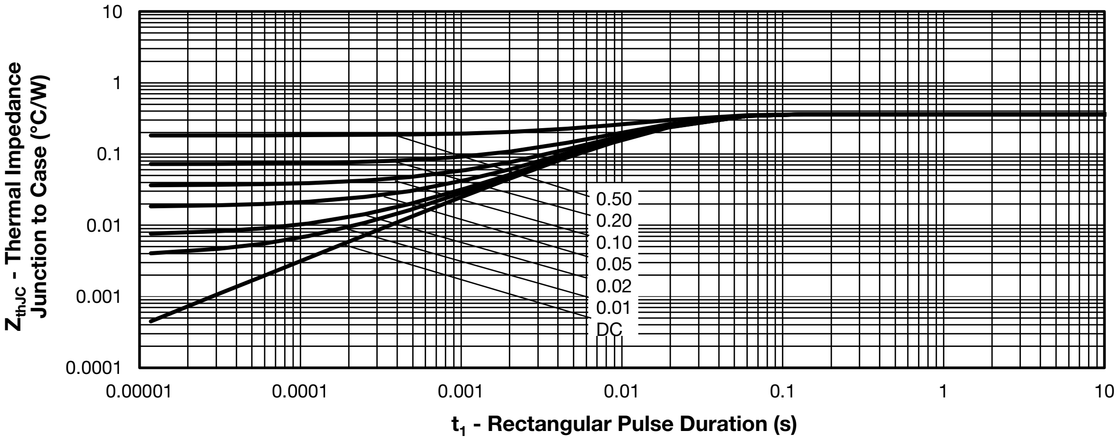


Fig. 17 - Z_{thJC} vs. t1 Rectangular Pulse Duration (Maximum Thermal Impedance Z_{thJC} Characteristics - (Q1 - Q4 Trench IGBT))

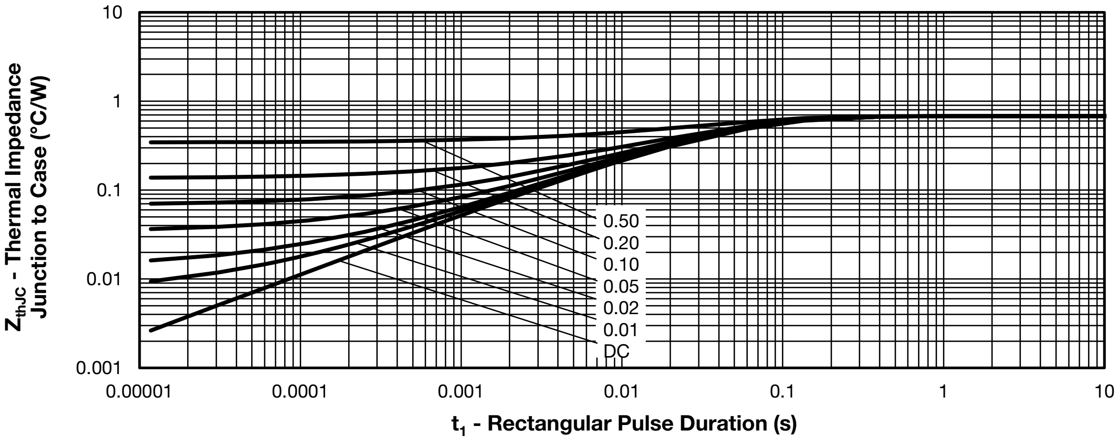


Fig. 18 - Z_{thJC} vs. t1 Rectangular Pulse Duration (Maximum Thermal Impedance Z_{thJC} Characteristics - (D5 - D6 Clamping Diode))

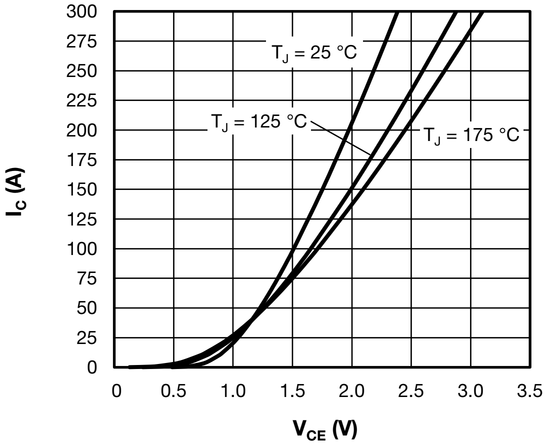


Fig. 19 - I_C vs. V_{CE}
(Typical Q2 - Q3 Trench IGBT Output Characteristics, V_{GE} = 15 V)

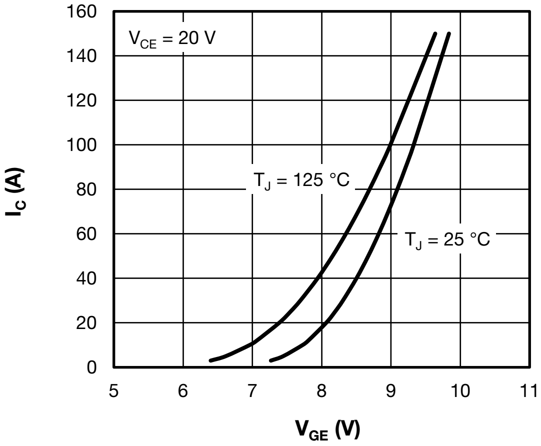


Fig. 22 - I_C vs. V_{GE}
(Typical Q2 - Q3 Trench IGBT Transfer Characteristics)

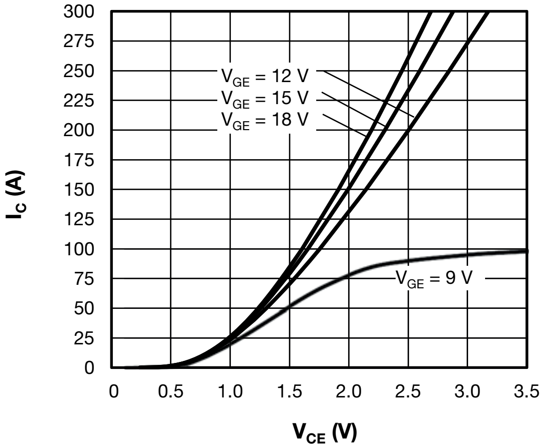


Fig. 20 - I_C vs. V_{CE} (Typical Q2 - Q3 Trench IGBT Output Characteristics, T_J = 125°C)

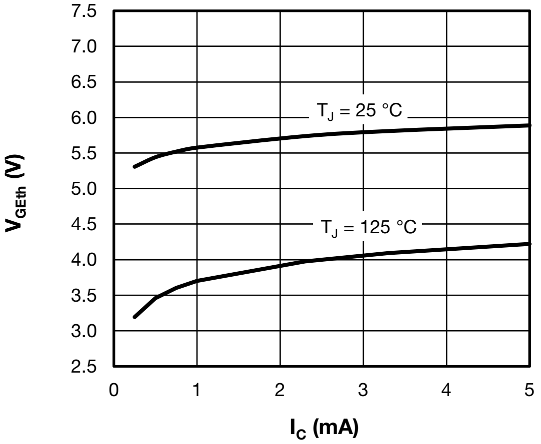


Fig. 23 - V_{GEth} vs. I_C
(Typical Q2 - Q3 Trench IGBT Gate Threshold Voltage)

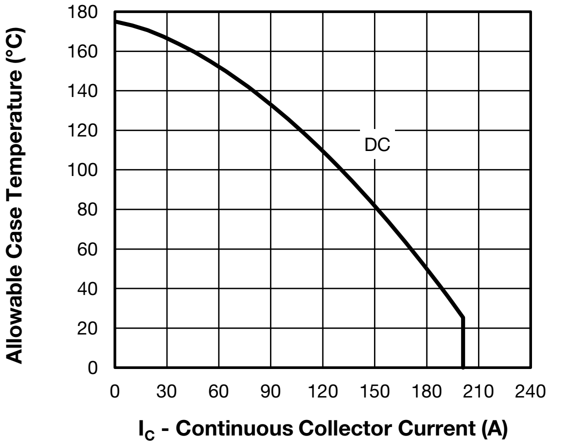


Fig. 21 - Allowable Case Temperature vs. Continuous Collector Current,
(Maximum Q2 - Q3 IGBT Continuous Collector Current vs. Case Temperature)

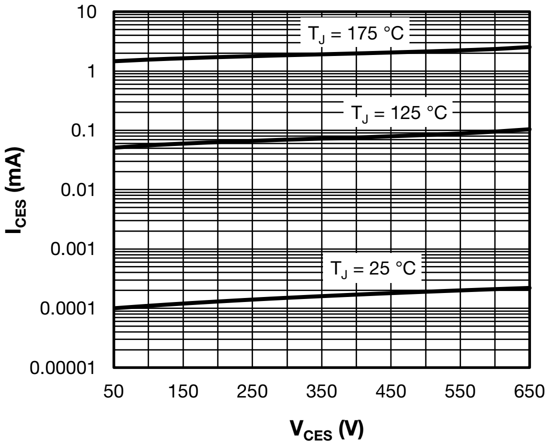


Fig. 24 - I_{CES} vs. V_{CES}
(Typical Q2 - Q3 Trench IGBT Zero Gate Voltage Collector Current)

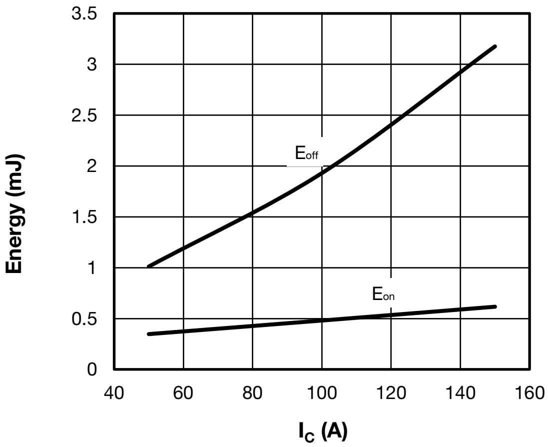


Fig. 25 - Energy Loss vs. I_C
(Typical Q2 - Q3 Trench IGBT Energy Loss vs. I_C (with D2 - D3 Antiparallel Diode)), T_J = 125 °C, V_{CC} = 325 V, R_g = 4.7 Ω, V_{GE} = ± 15 V, L = 500 µH

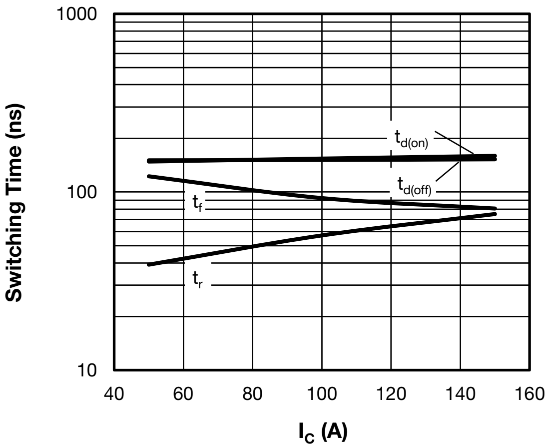


Fig. 26 - Switching Time vs. I_C
(Typical Q2 - Q3 Trench IGBT Switching Time vs. I_C (with D2 - D3 Antiparallel Diode)), T_J = 125 °C, V_{CC} = 325 V, R_g = 4.7 Ω, V_{GE} = ± 15 V, L = 500 µH

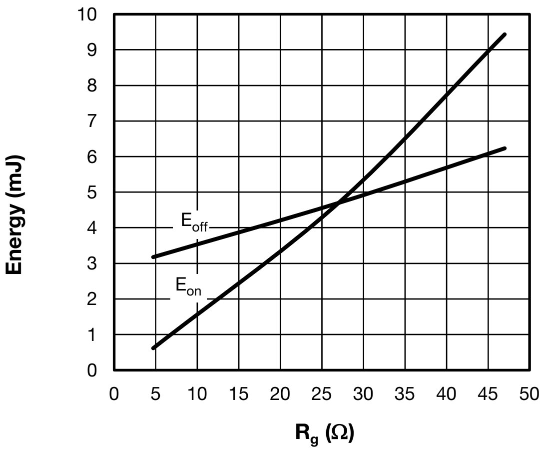


Fig. 27 - Energy Loss vs. R_g
(Typical Q2 - Q3 Trench IGBT Energy Loss vs. R_g (with D2 - D3 Antiparallel Diode)), T_J = 125 °C, V_{CC} = 325 V, I_C = 150 A, V_{GE} = ± 15 V, L = 500 µH

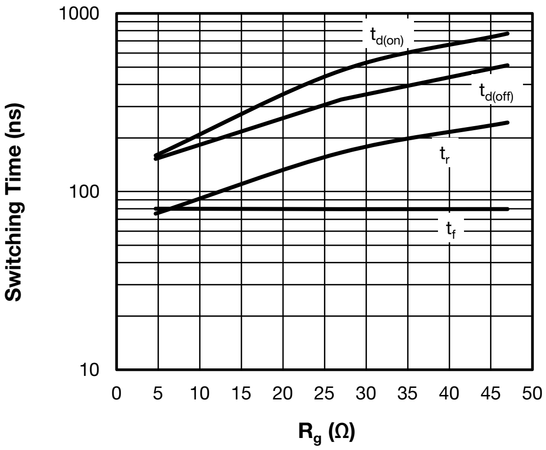


Fig. 28 - Switching Time vs. R_g (Typical Q2 - Q3 Trench IGBT Switching Time vs. R_g (with D2 - D3 Antiparallel Diode)), T_J = 125 °C, V_{CC} = 325 V, I_C = 150 A, V_{GE} = ± 15 V, L = 500 µH

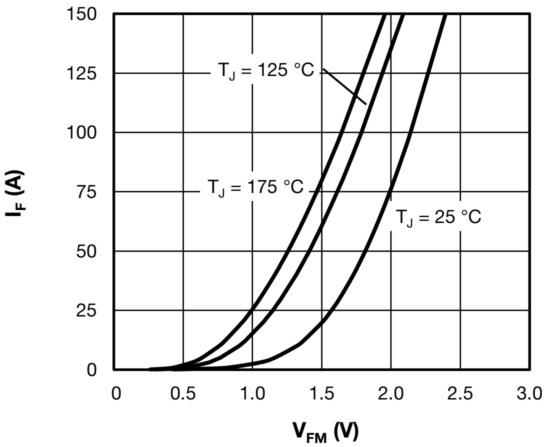


Fig. 29 - I_F vs. V_{FM}
(Typical D1 - D2 - D3 - D4 Antiparallel Diode Forward Characteristics)

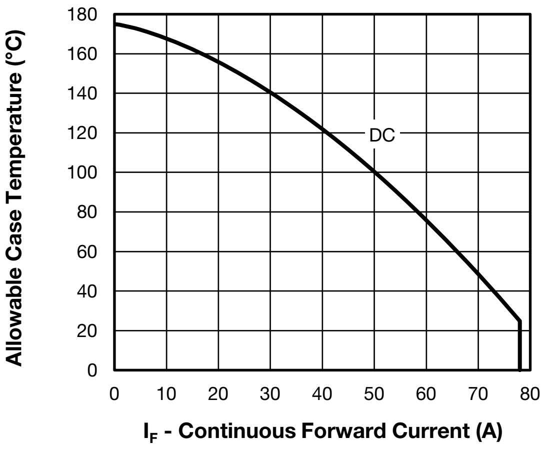


Fig. 30 - Allowable Case Temperature vs. Continuous Collector Current,
(Maximum D1- D2 - D3 - D4 Diode Continuous Forward Current vs. Case Temperature)

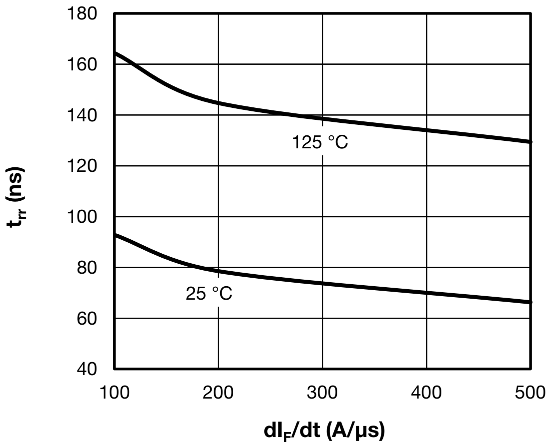


Fig. 31 - t_{rr} vs. dI_F/dt
(Typical D1 - D2 - D3 - D4 Antiparallel Diode Reverse Recovery Time vs. dI_F/dt), V_{rr} = 200 V, I_F = 50 A

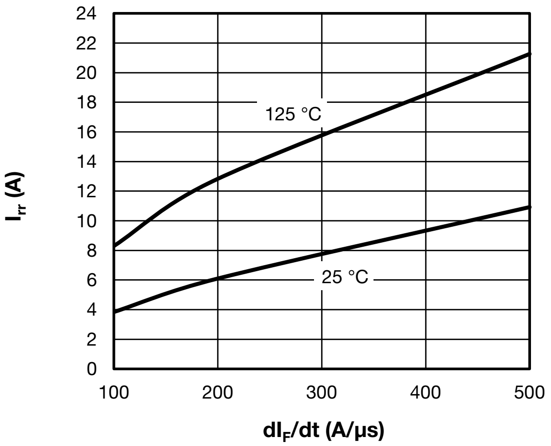


Fig. 32 - I_{rr} vs. dI_F/dt
(Typical D1 - D2 - D3 - D4 Antiparallel Diode Reverse Recovery Current vs. dI_F/dt), V_{rr} = 200 V, I_F = 50 A

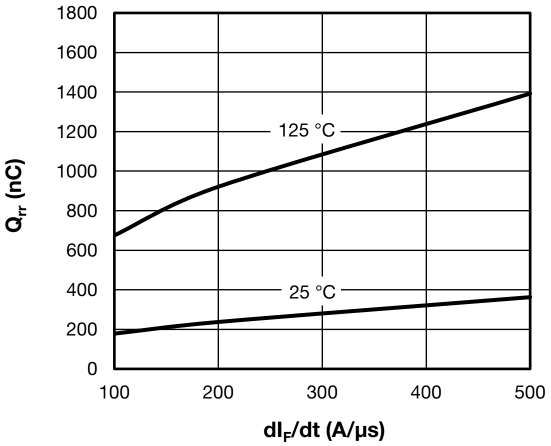


Fig. 33 - Q_{rr} vs. dI_F/dt
(Typical D1 - D2 - D3 - D4 Antiparallel Diode Reverse Recovery Charge vs. dI_F/dt), V_{rr} = 200 V, I_F = 50 A

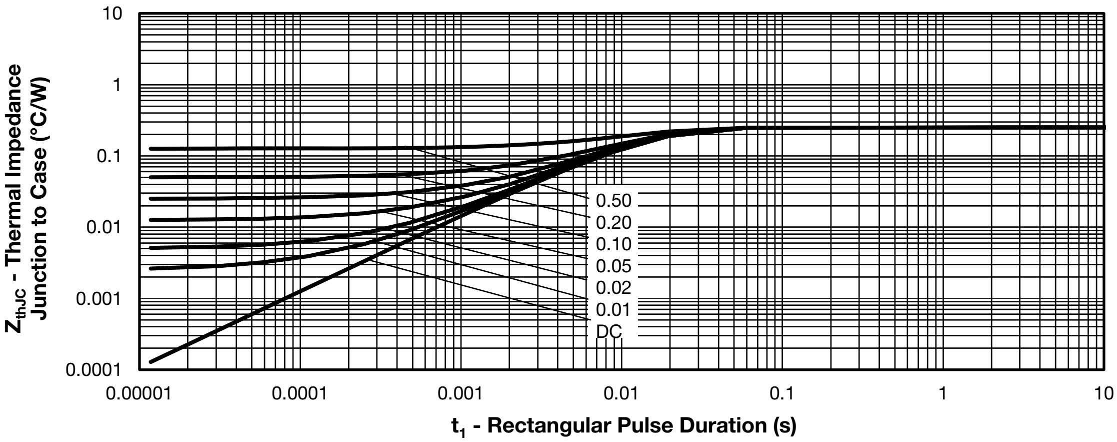


Fig. 34 - Z_{thJC} vs. t1 Rectangular Pulse Duration (Maximum Thermal Impedance Z_{thJC} Characteristics - (Q2 - Q3 Trench IGBT))

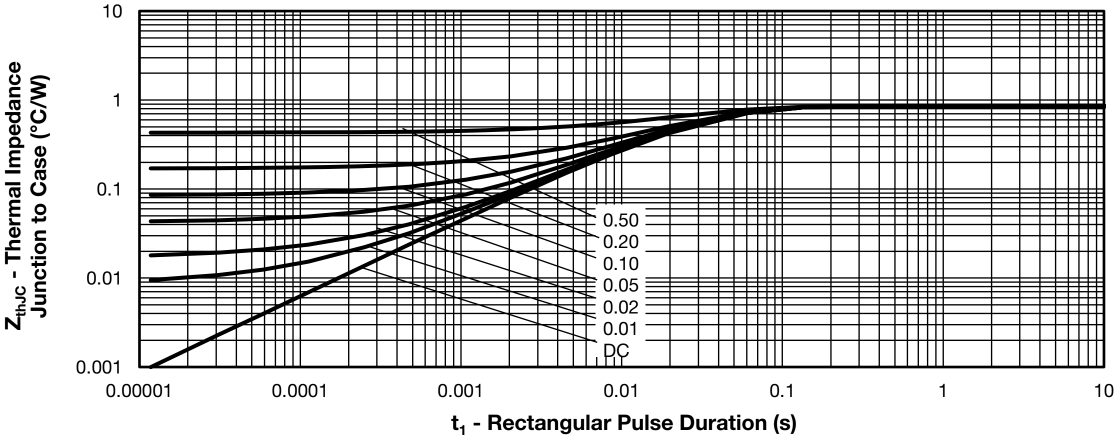


Fig. 35 - Z_{thJC} vs. t1 Rectangular Pulse Duration (Maximum Thermal Impedance Z_{thJC} Characteristics - (D1 - D2 - D3 - D4 Antiparallel Diode))

ORDERING INFORMATION TABLE

Device code	**VS-**	**ET**	**F**	**150**	**Y**	**65**	**U**
	①	②	③	④	⑤	⑥	⑦

1 - Vishay Semiconductors product

2 - Package indicator (ET = EMIPAK 2B)

3 - Circuit configuration (F = 3-levels half bridge inverter stage)

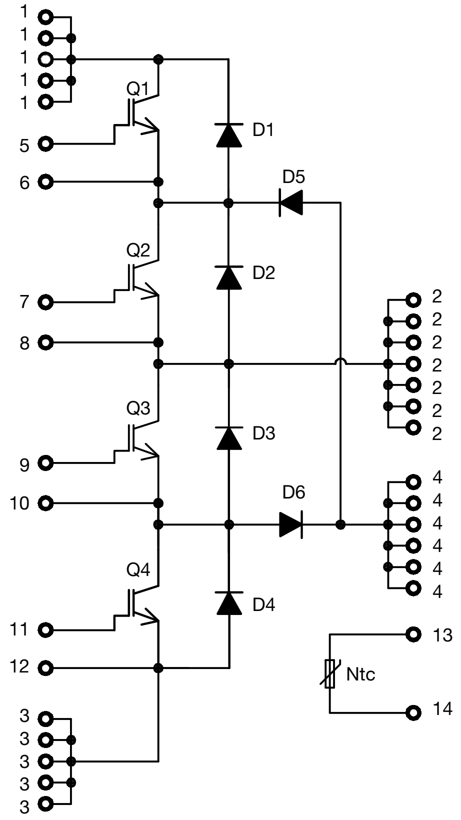
4 - Current rating (150 = 150 A)

5 - Switch die technology (Y = trench IGBT)

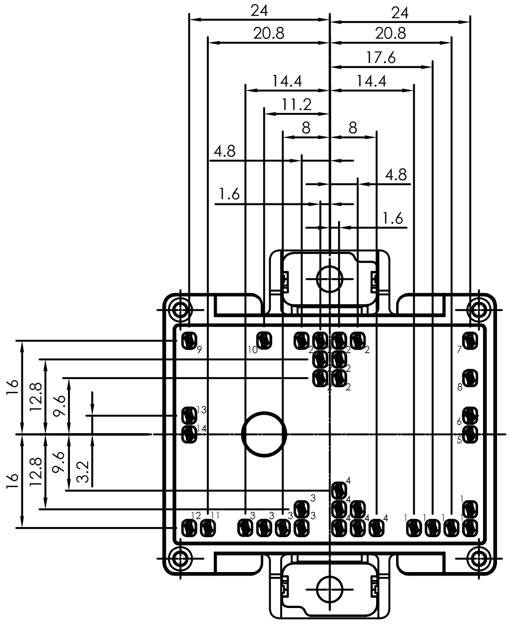
6 - Voltage rating (65 = 650 V)

7 - Diode die technology (U = ultrafast diode)

CIRCUIT CONFIGURATION



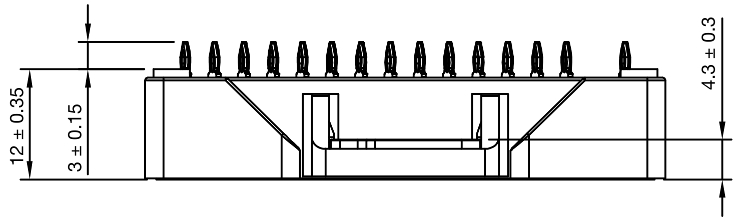
PACKAGE in millimeters

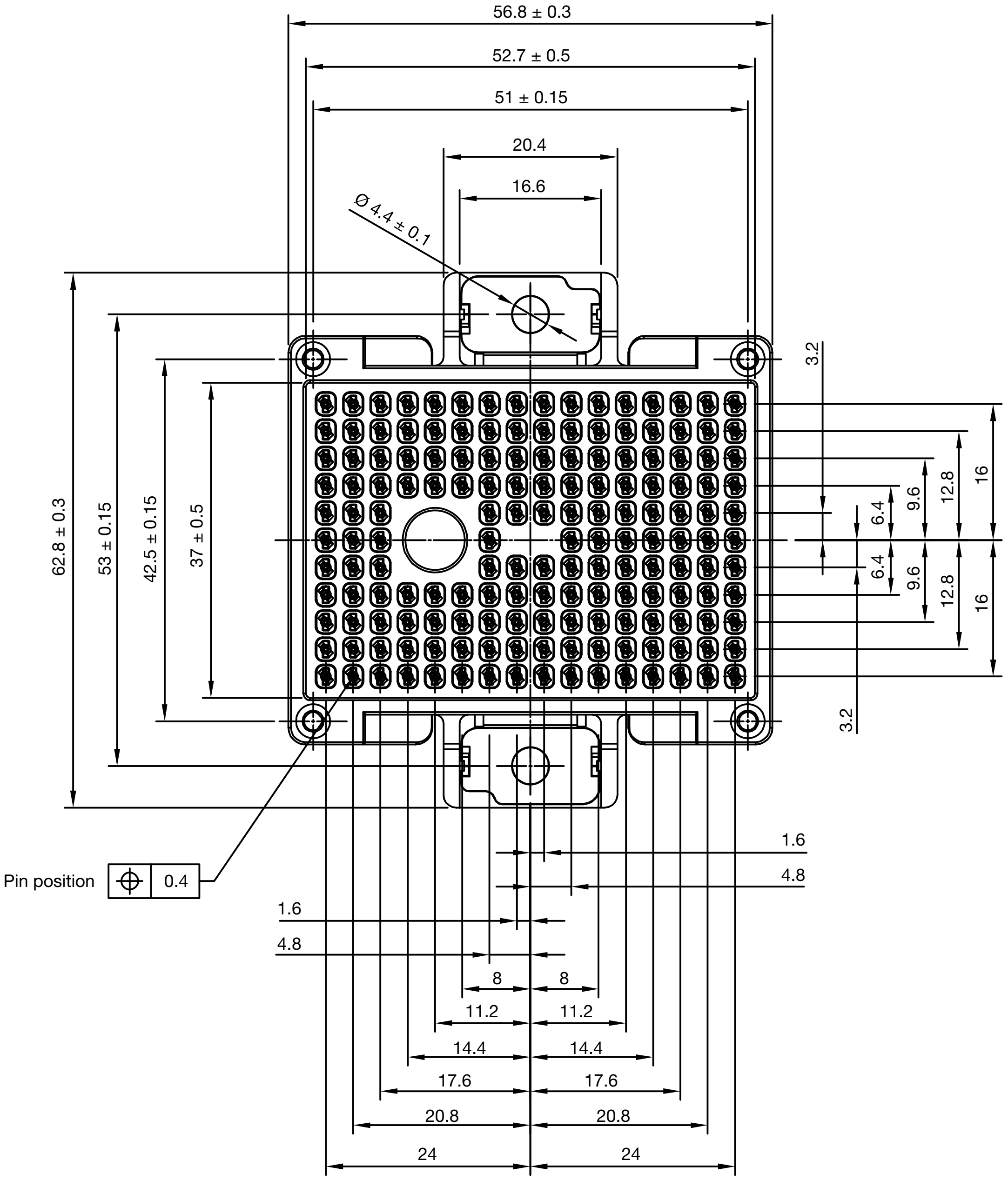


LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95559

EMIPAK-2B PressFit

DIMENSIONS in millimeters





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многоканальный
+7 495 668 12 70
info@moschip.ru

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9